Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-600 -500	mA
Continuous Drain Current (Note 6) V_{GS} = -1.8V	Steady State	T_A = +25°C T_A = +70°C	I_D	-400 -300	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-2	A
Maximum Body Diode Continuous Current			I_S	-800	mA

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	280	°C/W
Total Power Dissipation (Note 6)		P_D	0.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	140	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -1mA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-80 -100	nA	V_{DS} = -4.5V, V_{GS} = 0V V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10.0	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.7	1.0	Ω	V_{GS} = -4.5V, I_D = -100mA
		—	0.9	1.5		V_{GS} = -2.5V, I_D = -80mA
		—	1.2	2.0		V_{GS} = -1.8V, I_D = -40mA
		—	1.5	3.0		V_{GS} = -1.5V, I_D = -30mA
		—	5	—		V_{GS} = -1.2V, I_D = -1mA
Forward Transfer Admittance	$\|Y_{fs}\|$	—	0.7	—	s	V_{DS} = -3V, I_D = -100mA
Diode Forward Voltage	V_{SD}	—	-0.75	-1.2	V	V_{GS} = 0V, I_S = -330mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	46.1	—	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	7.2	—		
Reverse Transfer Capacitance	C_{rss}	—	4.9	—		
Total Gate Charge V_{GS} = -4.5V	Q_g	—	0.5	—	nC	V_{DS} = -10V, I_D = -250mA
Total Gate Charge V_{GS} = -8V	Q_g	—	0.8	—		
Gate-Source Charge	Q_{gs}	—	0.1	—		
Gate-Drain Charge	Q_{gd}	—	0.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	8.5	—	ns	V_{DD} = -3V, V_{GS} = -2.5V, R_L = 300Ω, R_g = 25Ω, I_D = -100mA
Turn-On Rise Time	t_R	—	4.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	20.2	—		
Turn-Off Fall Time	t_F	—	19.2	—		

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

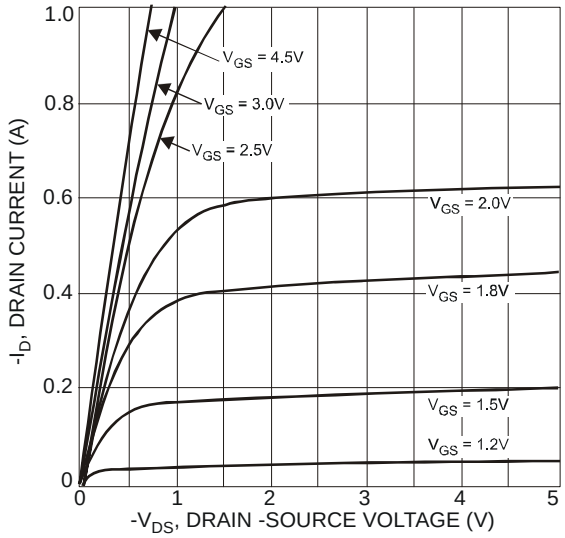


Fig. 1 Typical Output Characteristics

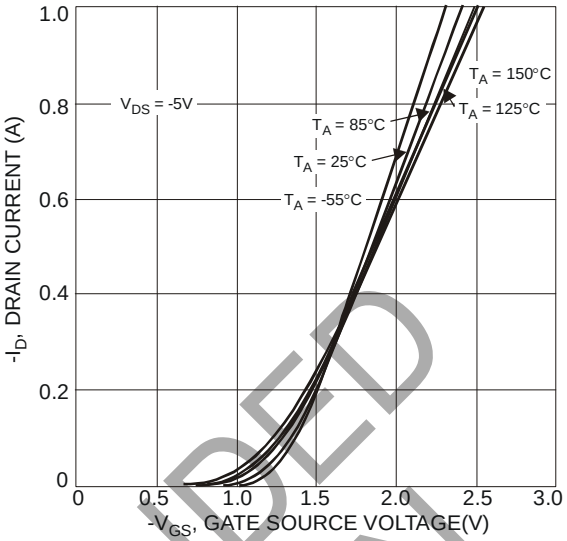


Fig. 2 Typical Transfer Characteristics

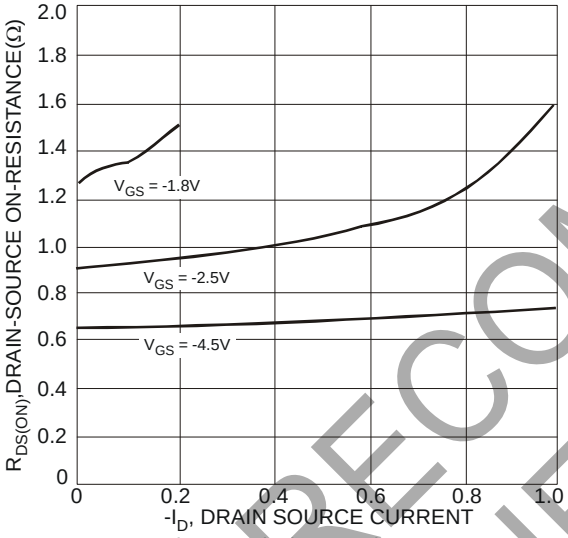


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

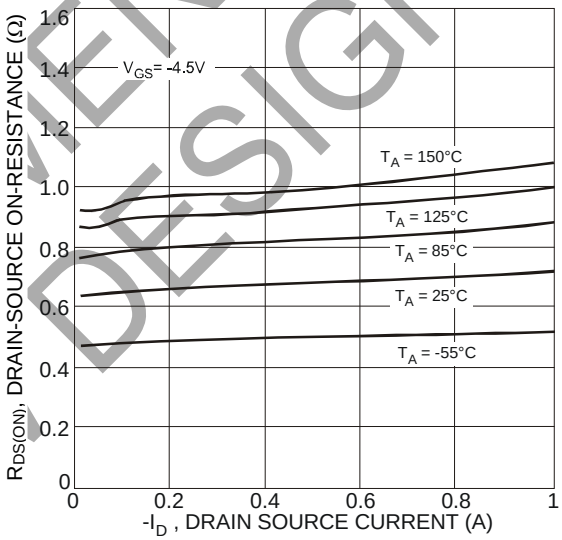


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

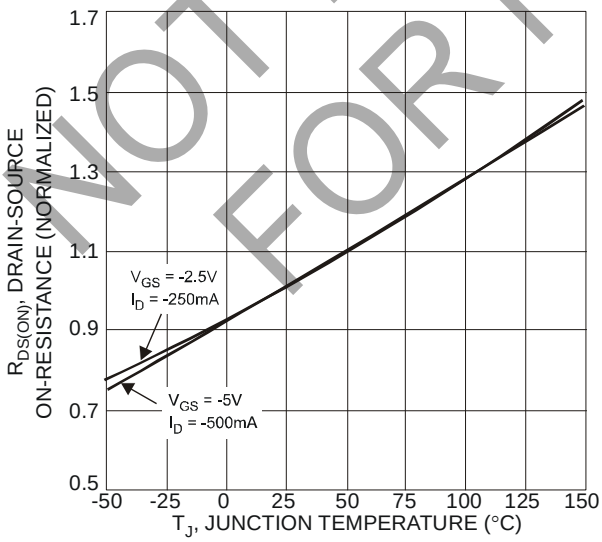


Fig. 5 On-Resistance Variation with Temperature

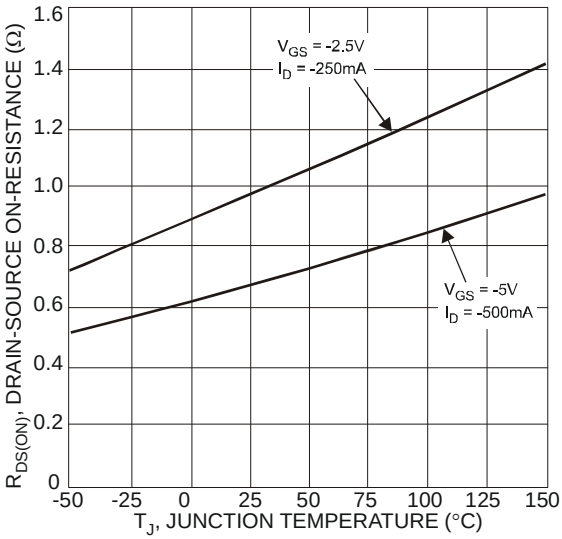


Fig. 6 On-Resistance vs.Temperature

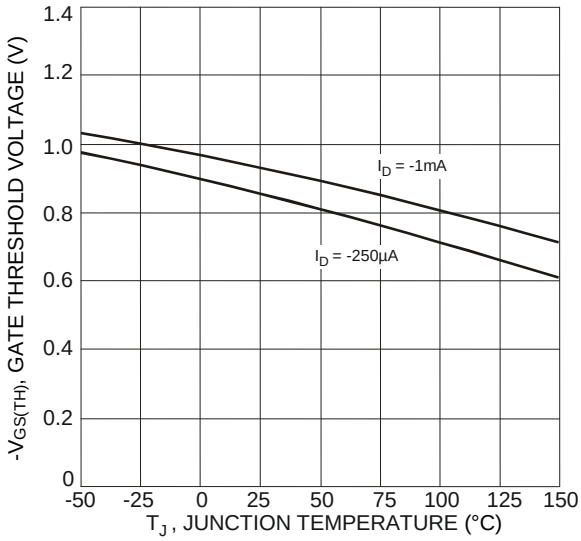


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

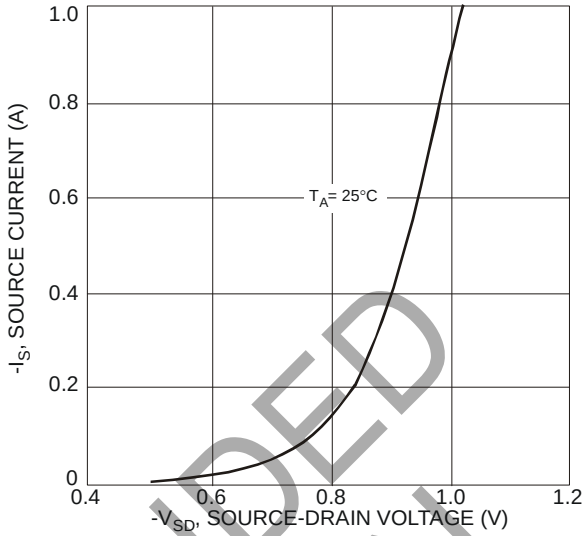


Fig. 8 Diode Forward Voltage vs. Current

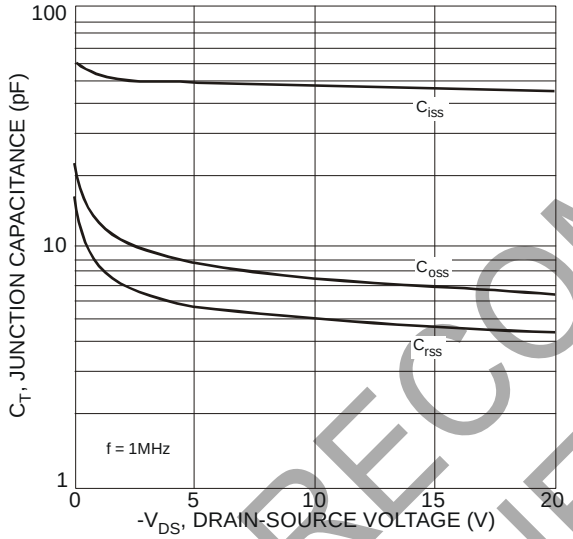


Fig. 9 Typical Junction Capacitance

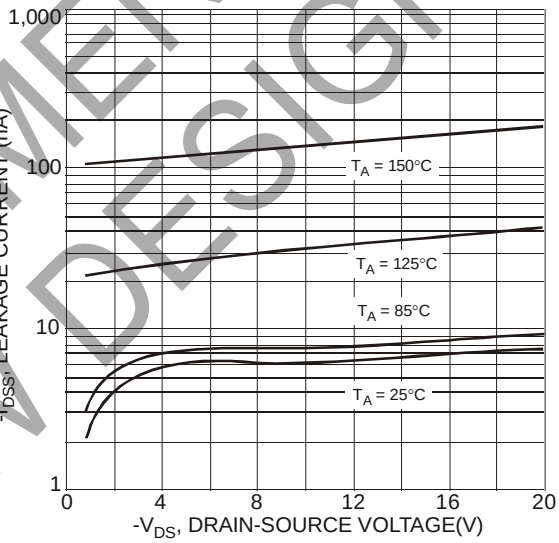


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

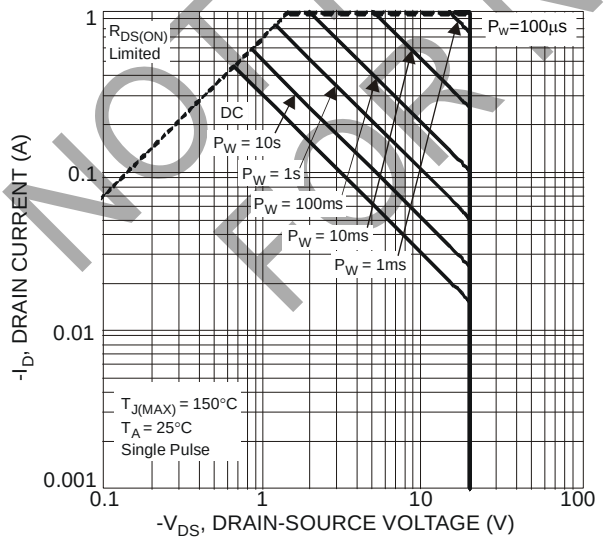


Fig. 11 SOA, Safe Operation Area

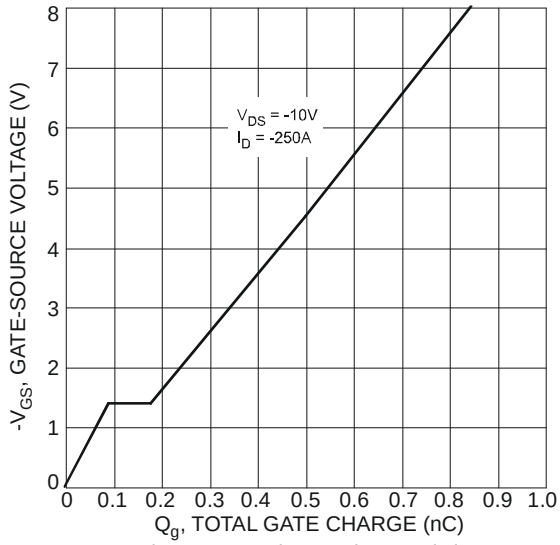
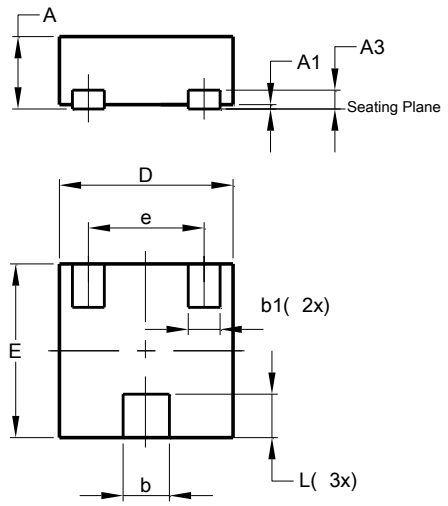


Fig. 12 Gate-Charge Characteristics

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1212-3

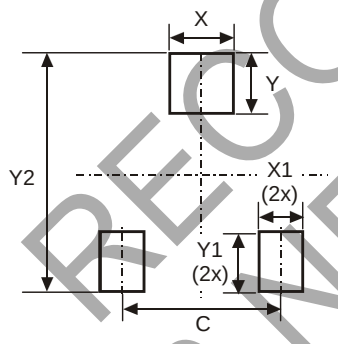


X1-DFN1212-3			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	-	-	0.13
b	0.27	0.37	0.32
b1	0.17	0.27	0.22
D	1.15	1.25	1.20
E	1.15	1.25	1.20
e	-	-	0.80
L	0.25	0.35	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1212-3



Dimensions	Value (in mm)
C	0.80
X	0.42
X1	0.32
Y	0.50
Y1	0.50
Y2	1.50

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